● General Description

The AGM605A combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

● Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

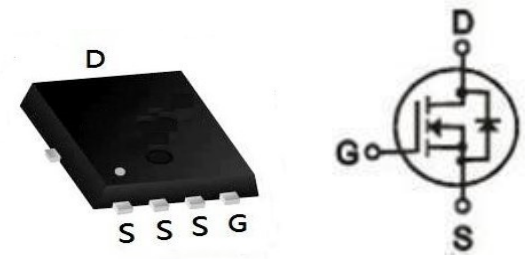
● Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
60V	4.5mΩ	72A

PDFN5*6 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM605A	AGM605A	PDFN5*6	----	----	3000

Table 1. Absolute Maximum Ratings (TA=25℃)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	60	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25℃) **(Note 1)**	72	A
	Drain Current-Continuous(Tc=100℃)	45	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed **(Note 2)**	310	A
PD	Maximum Power Dissipation(Tc=25℃)	25	w
	Maximum Power Dissipation(Tc=100℃)	10	w
EAS	Avalanche energy **(Note 3)**	20	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	℃

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State)[1]	---	50	℃/W
RθJC	Thermal Resistance Junction-Case[1]	---	5	℃/W

Table 3. Electrical Characteristics (TA=25℃unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	60	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=60V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	VDS=VGS,ID=250μA	1	1.8	2.5	V
gFS	Forward Transconductance	VDS=5V,ID=20A	--	28	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=20A	--	4.5	5.5	mΩ
		VGS=4.5V, ID=15A	--	6.7	9.8	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=25V,VGS=0V, F=1MHZ	--	2413	--	pF
Coss	Output Capacitance		--	434	--	pF
Crss	Reverse Transfer Capacitance		--	29	--	pF
Rg	Gate resistance	VGS=0V, VDS=-0V,f=1.0MHz	--	1.3	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V,VDS=30V, RD=5Ω,RGEN=10Ω	--	18	--	nS
tr	Turn-on Rise Time		--	2	--	nS
td(off)	Turn-Off Delay Time		--	56	--	nS
tf	Turn-Off Fall Time		--	18	--	nS
Qg	Total Gate Charge	VGS=0V, VDS=30V, ID=20A	--	44.5	--	nC
Qgs	Gate-Source Charge		--	11.3	--	nC
Qgd	Gate-Drain Charge		--	7.7	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	72	A
VSD	Forward on Voltage	VGS=0V,IS=20A	--	--	1.2	V
trr	Reverse Recovery Time	IF=20A , dI/dt=100A/μs , TJ=25℃	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25℃

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

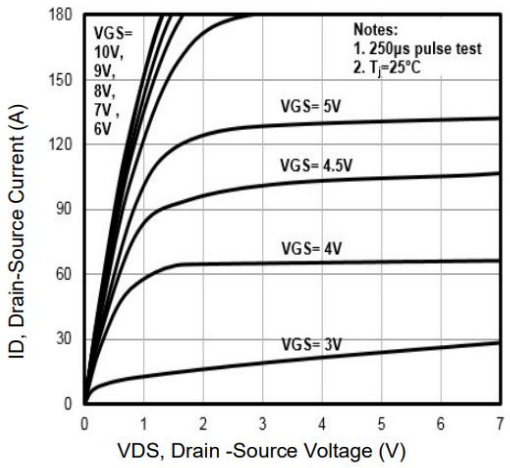


Fig1. Typical Output Characteristics

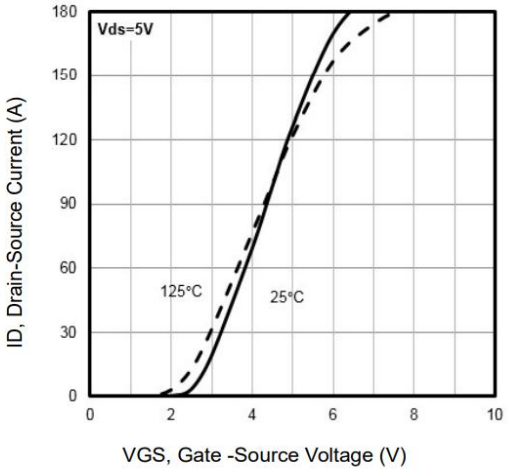


Fig2. Typical Transfer Characteristics

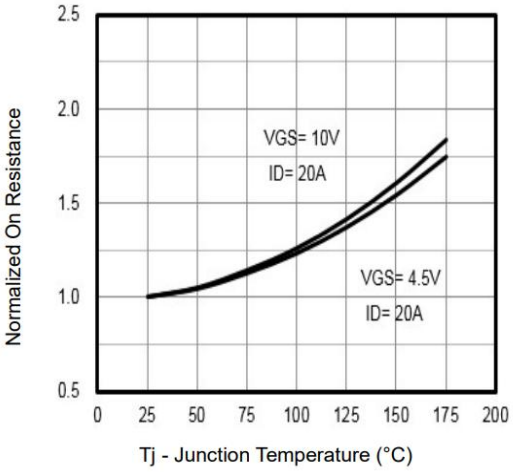


Fig3. Normalized On-Resistance Vs. Temperature

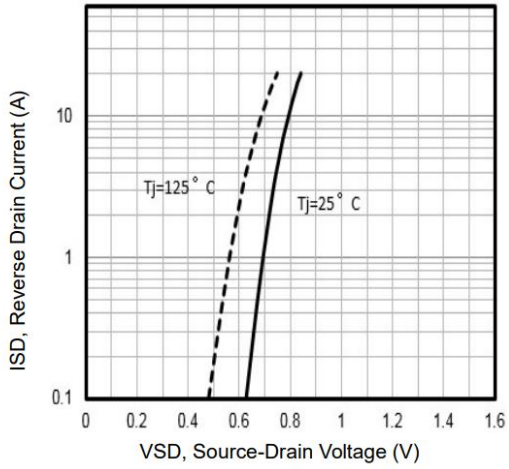


Fig4. Typical Source-Drain Diode Forward Voltage

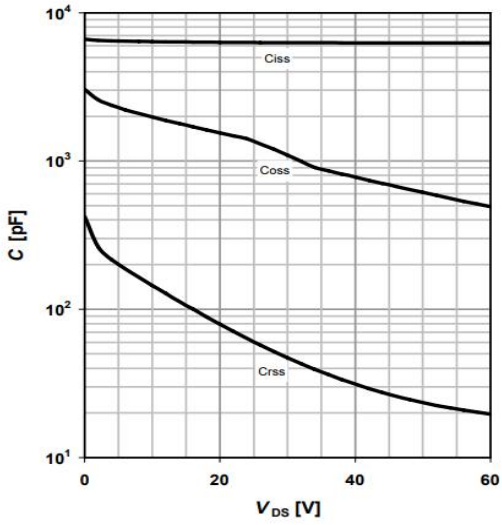


Fig5. Typ.Capacitance

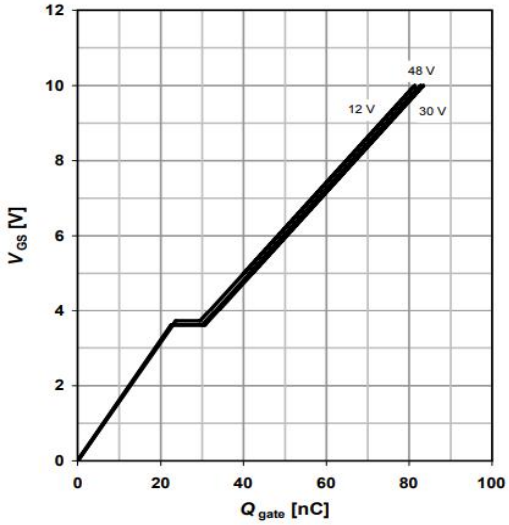


Fig6. Typ.Gate Charge

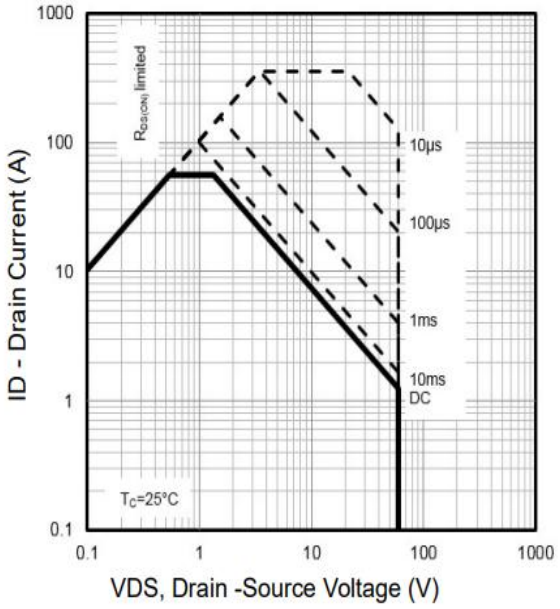


Fig7. Safe Operating Area

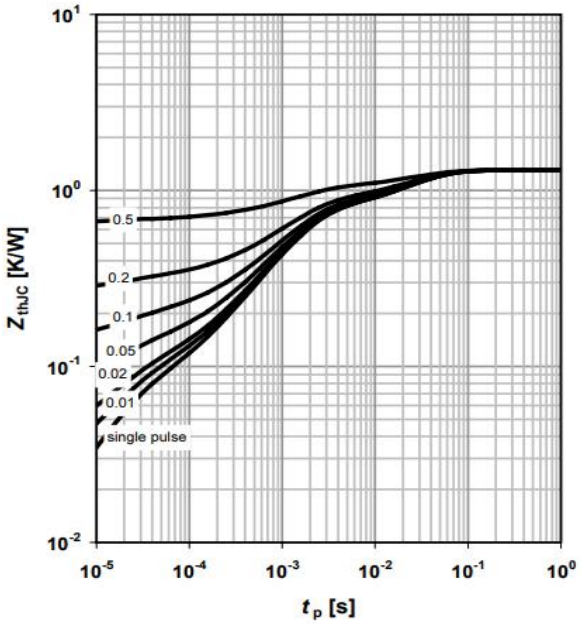


Fig8. Max. transient thermal impedance

Test

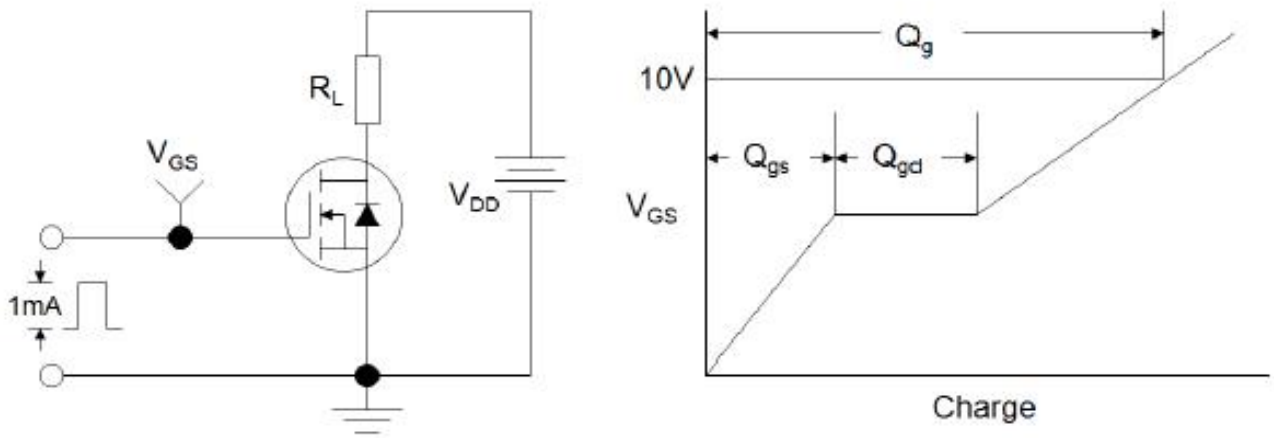


Figure1:Gate Charge Test Circuit & Waveform

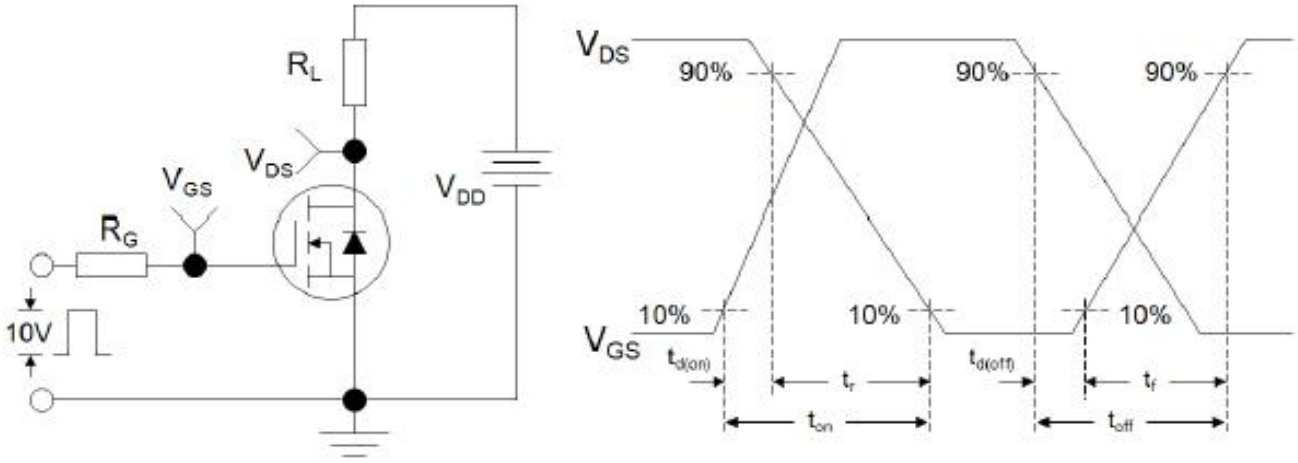


Figure 2: Resistive Switching Test Circuit & Waveforms

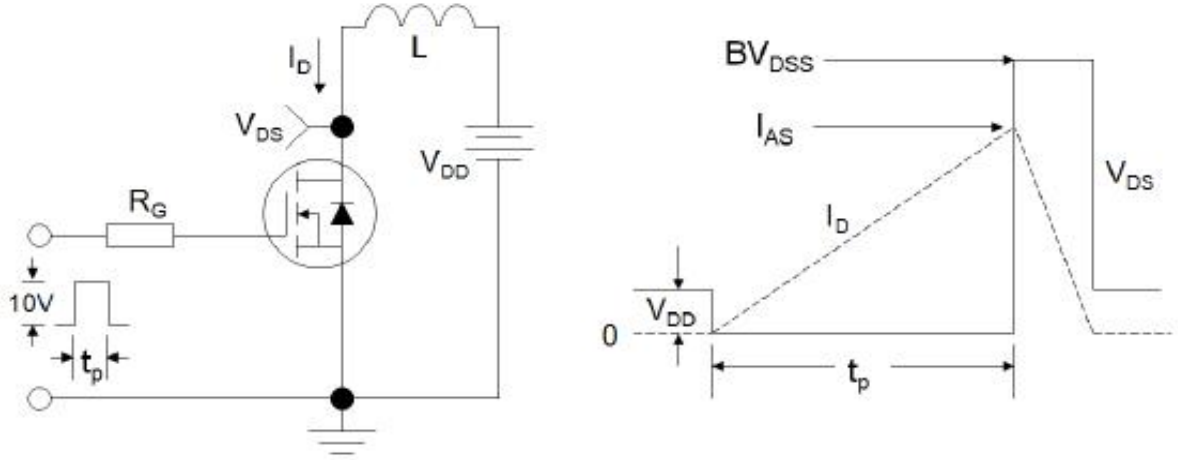
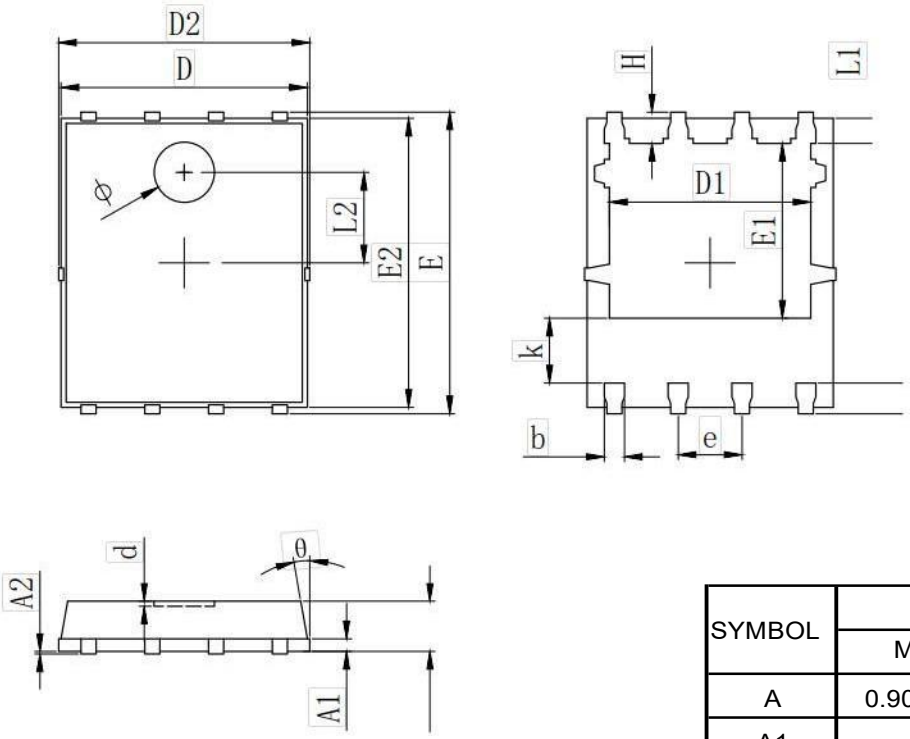


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

•Dimensions（DFN5×6）



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.900	1.000	1.100
A1		0.254 REF.	
A2		0~0.05	
D	4.824	4.900	4.976
D1	3.910	4.010	4.110
D2	4.924	5.000	5.076
E	5.924	6.000	6.076
E1	3.375	3.475	3.575
E2	5.674	5.750	5.826
b	0.350	0.400	0.450
e		1.270 TYP.	
L	0.534	0.610	0.686
L1	0.424	0.500	0.576
L2		1.800 REF.	
k	1.190	1.290	1.390
H	0.549	0.625	0.701
θ	8°	10°	12°
ϕ	1.100	1.200	1.300
d			0.100

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